

High Current MegaMOS™ FET

IXTK 74 N20
IXTH 68 N20

V_{DSS}	I_{D25}	$R_{DS(on)}$
200 V	74 A	35 mΩ
200 V	68 A	35 mΩ

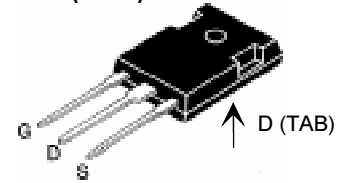
N-Channel Enhancement Mode

Preliminary data

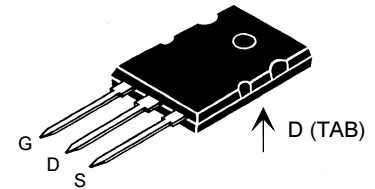


Symbol	Test conditions	Maximum ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	200	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1.0\text{ M}\Omega$	200	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	74N20	74 A
		68N20	68 A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	74N20	296 A
		68N20	272 A
P_D	$T_C = 25^\circ\text{C}$	74N20	416 W
		68N20	300 W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight		TO-264	10 g
		TO-247	6 g
Max lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$

TO-247AD (IXTH)



TO-264 AA (IXTK)



G = Gate D = Drain
S = Source Tab = Drain

Features

- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- International standard package
- Fast switching times

Applications

- Motor controls
- DC choppers
- Uninterruptable Power Supplies (UPS)
- Switch-mode and resonant-mode

Advantages

- Easy to mount with one screw (isolated mounting screw hole)
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
V_{DSS}	$V_{GS} = 0\text{ V}$, $I_D = 5\text{ mA}$	200		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4\text{ mA}$	2.0		V
I_{GSS}	$V_{GS} = \pm 20\text{ V DC}$, $V_{DS} = 0$			$\pm 100\text{ nA}$
I_{DSS}	$V_{DS} = 0.8 V_{DSS}$ $V_{GS} = 0\text{ V}$		$T_J = 25^\circ\text{C}$	500 μA
			$T_J = 125^\circ\text{C}$	3 mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300\text{ ms}$, duty cycle $d \leq 2\%$			35 mΩ

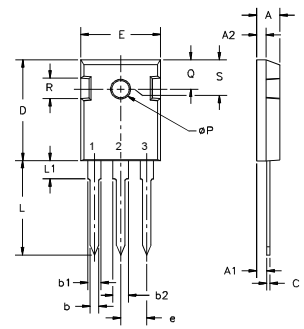
Symbol	Test Conditions	Characteristic values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 0.5 I_{D25}$, pulse test	35	42	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		5450	pF
C_{oss}			1275	pF
C_{rss}			630	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 1\ \Omega$ (External)		30	ns
t_r			230	ns
$t_{d(off)}$			180	ns
t_f			50	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$		300	nC
Q_{gs}			75	nC
Q_{gd}			100	nC
R_{thJC}	TO-264 AA		0.30	K/W
R_{thCK}			0.15	K/W
R_{thJC}	TO-247 AD		0.35	K/W
R_{thCK}			0.15	K/W

Source-Drain Diode

Ratings and Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Conditions	Min.	Typ.	Max.
I_S	$V_{GS} = 0$	74N20 68N20		74 68 A
I_{SM}	Repetitive; pulse width limited by T_{JM}	74N20 68N20		296 272 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.5 V
t_{rr}	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$		600	ns

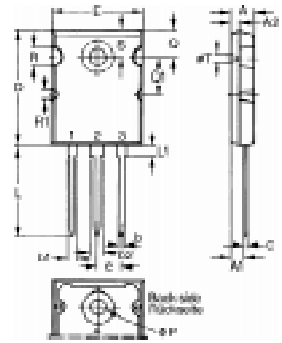
TO-247 AD (IXTH) Outline



Terminals: 1 - Gate 2 - Drain
3 - Source Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

TO-264 AA Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A ₁	2.54	2.89	.100	.114
A ₂	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b ₁	2.39	2.69	.094	.106
b ₂	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e		5.46 BSC		.215 BSC
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072